

N- and P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
N-Channel	30	0.015 at V _{GS} = 10 V	18	12.5
		0.020 at V _{GS} = 4.5 V	14	
P-Channel	-30	0.039 at V _{GS} = -10 V	-12	5
		0.060 at V _{GS} = -4.5 V	-8	

FEATURES

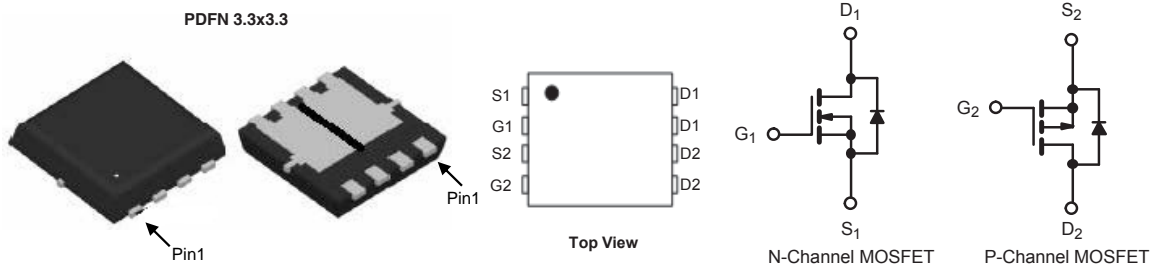
- DT-Trench Power MOSFET
- 100% R_g and UIS Tested

APPLICATIONS

- Networking DC-DC Power System
- Load Switch



RoHS
COMPLIANT



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	V _{DS}	30	-30	V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	18	-12	A
		T _C = 70 °C	15	-8	
		T _A = 25 °C	12 ^{b, c}	-8.3 ^{b, c}	
		T _A = 70 °C	9.4 ^{b, c}	-6.5 ^{b, c}	
Pulsed Drain Current	I _{DM}	72	-48	A	
Source-Drain Current Diode Current	I _S	T _C = 25 °C	15		-10
		T _A = 25 °C	8 ^{b, c}		-5 ^{b, c}
Pulsed Source-Drain Current	I _{SM}	72	-48	mJ	
Single Pulse Avalanche Current	I _{AS}	40	-27		
Single Pulse Avalanche Energy	E _{AS}	20	-12	W	
Maximum Power Dissipation	P _D	T _C = 25 °C	12.5		6
		T _C = 70 °C	5		2.9
		T _A = 25 °C	4.3 ^{b, c}		2.0 ^{b, c}
		T _A = 70 °C	2.25 ^{b, c}	1.25 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150		°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	54	64	25	30	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	70	85	50	60		

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 120 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	N-Ch	30			V
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-30			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		44		mV/ $^\circ\text{C}$
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		-42		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		-5.5		
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		4.6		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	1		3	V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-1		-3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch			100	nA
			P-Ch			-100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1	
		$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			10	
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-10	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	72			A
		$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	-48			
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	N-Ch		0.015	0.018	Ω
		$V_{GS} = -10\text{ V}, I_D = -8\text{ A}$	P-Ch		0.039	0.047	
		$V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	N-Ch		0.020	0.025	
		$V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$	P-Ch		0.060	0.067	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$	N-Ch		25		S
		$V_{DS} = -15\text{ V}, I_D = -8\text{ A}$	P-Ch		12		
Dynamic^a							
Input Capacitance	C_{iss}	N-Channel $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		650		μF
Output Capacitance	C_{oss}		P-Ch		570		
Reverse Transfer Capacitance	C_{rss}		P-Channel $V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		190	
		P-Ch			80		
Total Gate Charge	Q_g	$V_{DS} = 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	N-Ch		12.5	22	nC
		$V_{DS} = -24\text{ V}, V_{GS} = -10\text{ V}, I_D = -8\text{ A}$	P-Ch		5	18	
		N-Channel $V_{DS} = 24\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	N-Ch		5.3	9	
			P-Ch		1.8	3	
Gate-Source Charge	Q_{gs}	P-Channel $V_{DS} = -24\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$	N-Ch		1.4		
P-Ch			0.55				
Gate-Drain Charge	Q_{gd}	N-Ch		1.9			
		P-Ch		1.1			
Gate Resistance	R_g	$f = 1\text{ MHz}$	N-Ch	0.5	2.0	4.5	Ω
			P-Ch	1.0	3.5	11	

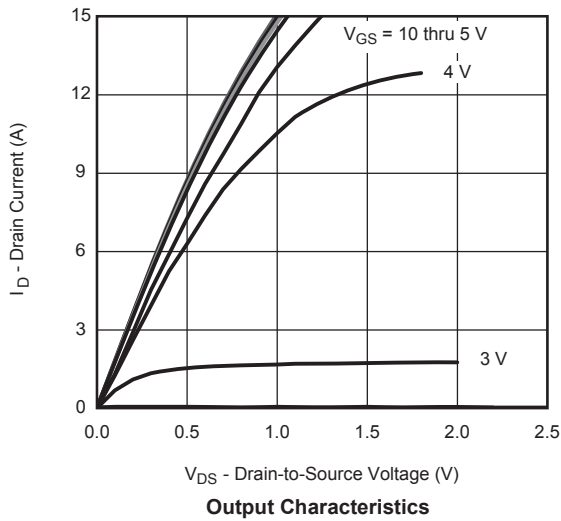
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Dynamic^a							
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 24\text{ V}$, $R_L = 4\ \Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch		7	14	ns
			P-Ch		8	17	
Rise Time	t_r		N-Ch		10	25	
			P-Ch		13	27	
Turn-Off Delay Time	$t_{d(off)}$	P-Channel $V_{DD} = -24\text{ V}$, $R_L = 4\ \Omega$ $I_D \cong -8\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 1\ \Omega$	N-Ch		15	32	
			P-Ch		33	65	
Fall Time	t_f		N-Ch		9	22	
			P-Ch		9	23	
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 24\text{ V}$, $R_L = 4\ \Omega$ $I_D \cong 8\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$	N-Ch		16	30	
			P-Ch		47	80	
Rise Time	t_r		N-Ch		19	30	
			P-Ch		33	50	
Turn-Off Delay Time	$t_{d(off)}$	P-Channel $V_{DD} = -24\text{ V}$, $R_L = 4\ \Omega$ $I_D \cong -5\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_g = 1\ \Omega$	N-Ch		16	30	
			P-Ch		28	60	
Fall Time	t_f		N-Ch		10	20	
			P-Ch		13	25	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	N-Ch			15	A
			P-Ch			-10	
Pulse Diode Forward Current ^a	I_{SM}		N-Ch			72	
			P-Ch			-48	
Body Diode Voltage	V_{SD}	$I_S = 1.6\text{ A}$	N-Ch		0.78	1.2	V
		$I_S = -1.6\text{ A}$	P-Ch		-0.76	-1.2	
Body Diode Reverse Recovery Time	t_{rr}	N-Channel $I_F = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$	N-Ch		7	34	ns
			P-Ch		5	55	
Body Diode Reverse Recovery Charge	Q_{rr}		N-Ch		4	25	nC
			P-Ch		1.5	35	
Reverse Recovery Fall Time	t_a	P-Channel $I_F = -2\text{ A}$, $di/dt = -100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$	N-Ch		17		ns
			P-Ch		19		
Reverse Recovery Rise Time	t_b		N-Ch		6		
			P-Ch		15		

Notes:

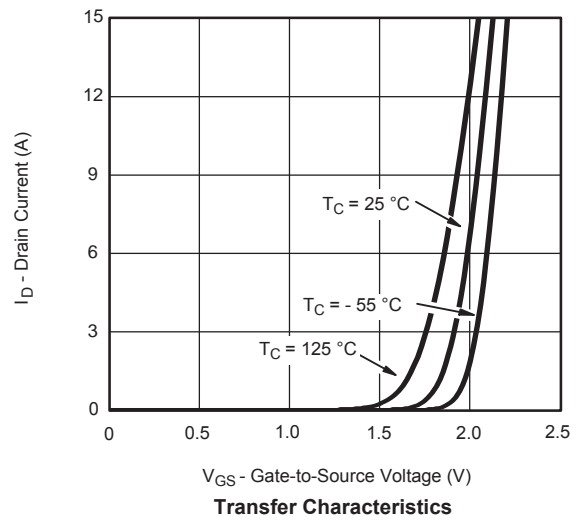
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

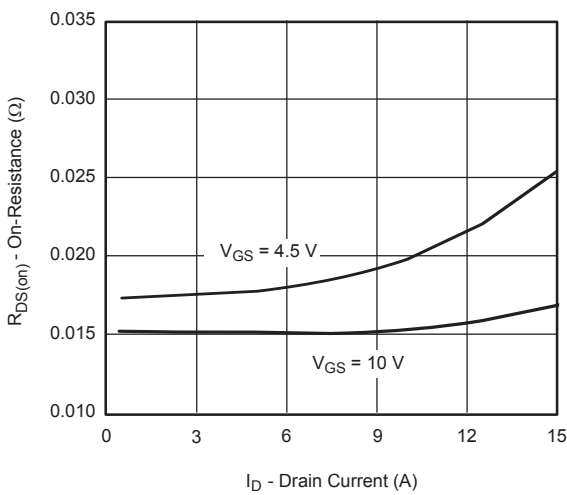
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



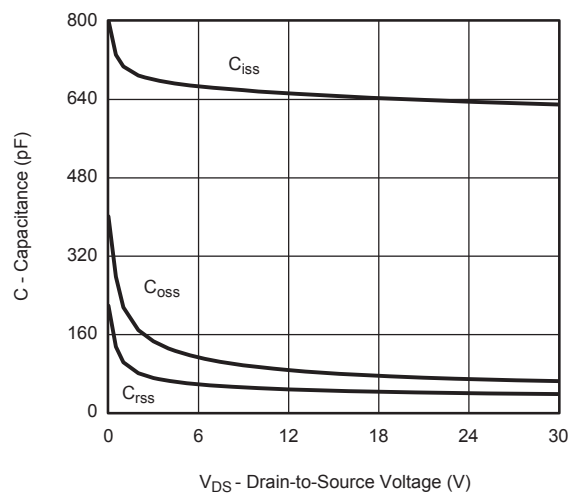
Output Characteristics



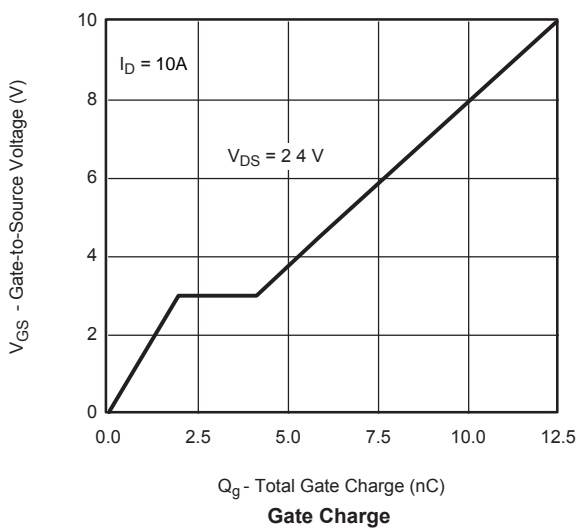
Transfer Characteristics



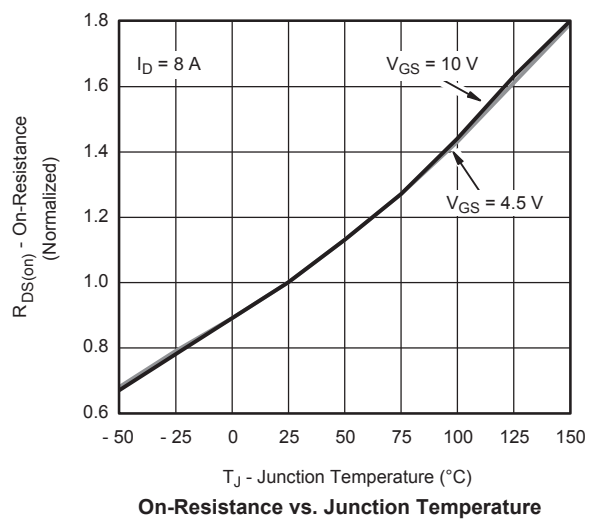
On-Resistance vs. Drain Current



Capacitance

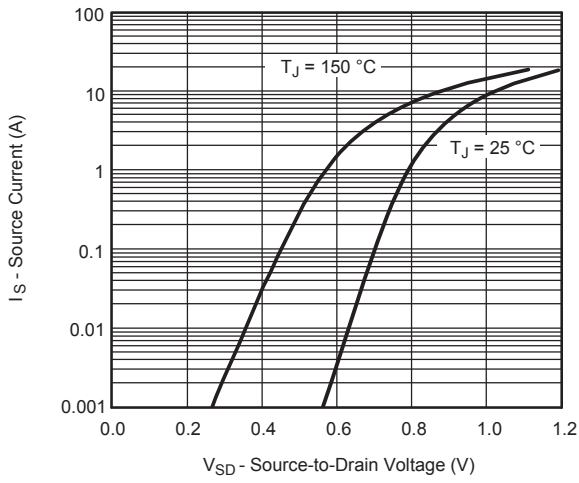


Gate Charge

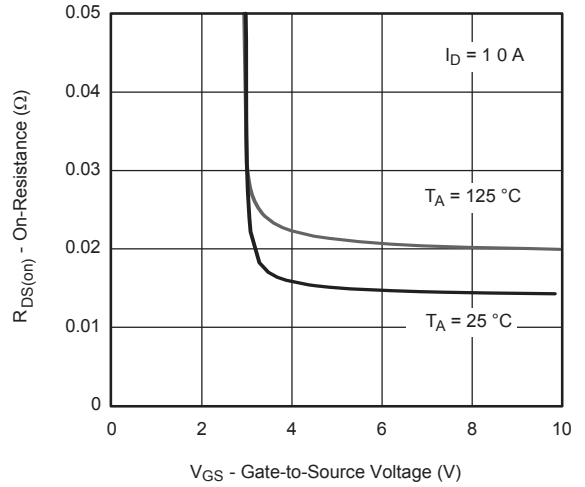


On-Resistance vs. Junction Temperature

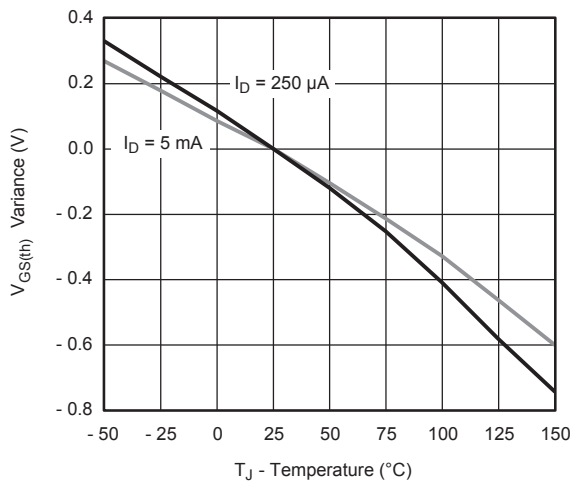
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



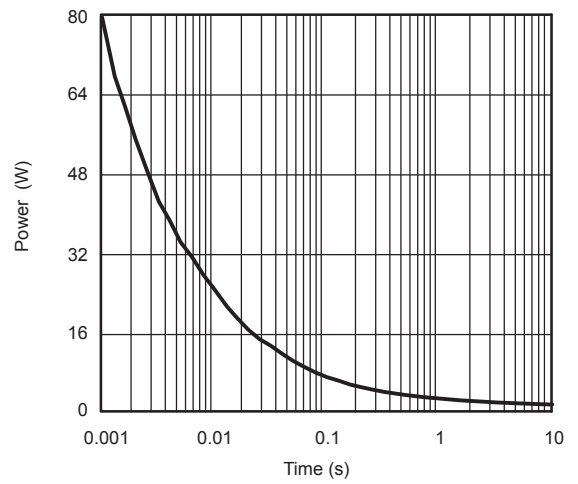
Source-Drain Diode Forward Voltage



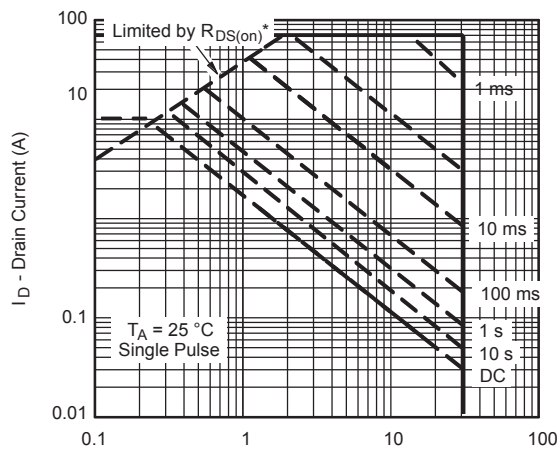
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

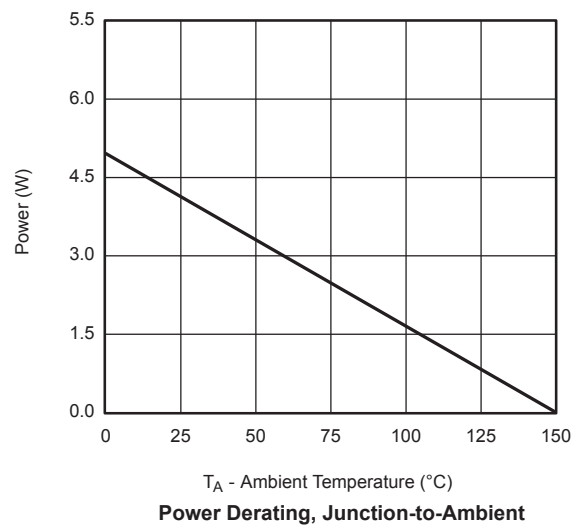
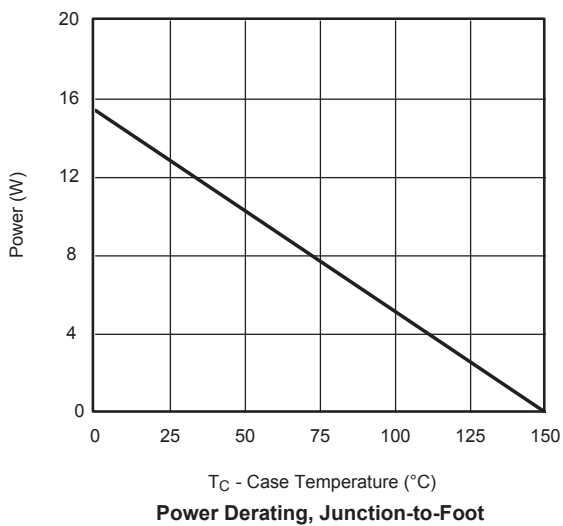
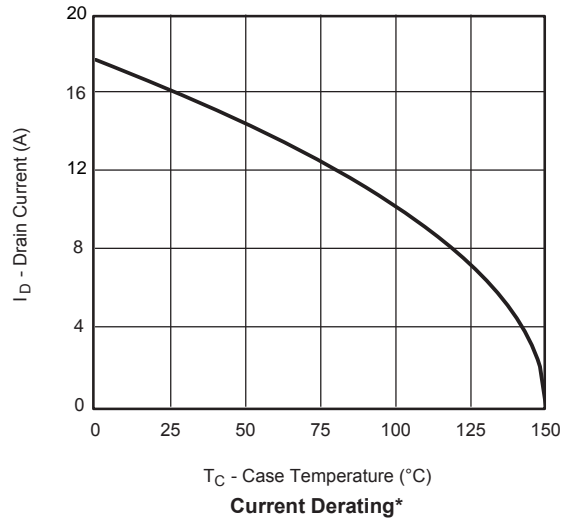


Single Pulse Power, Junction-to-Ambient



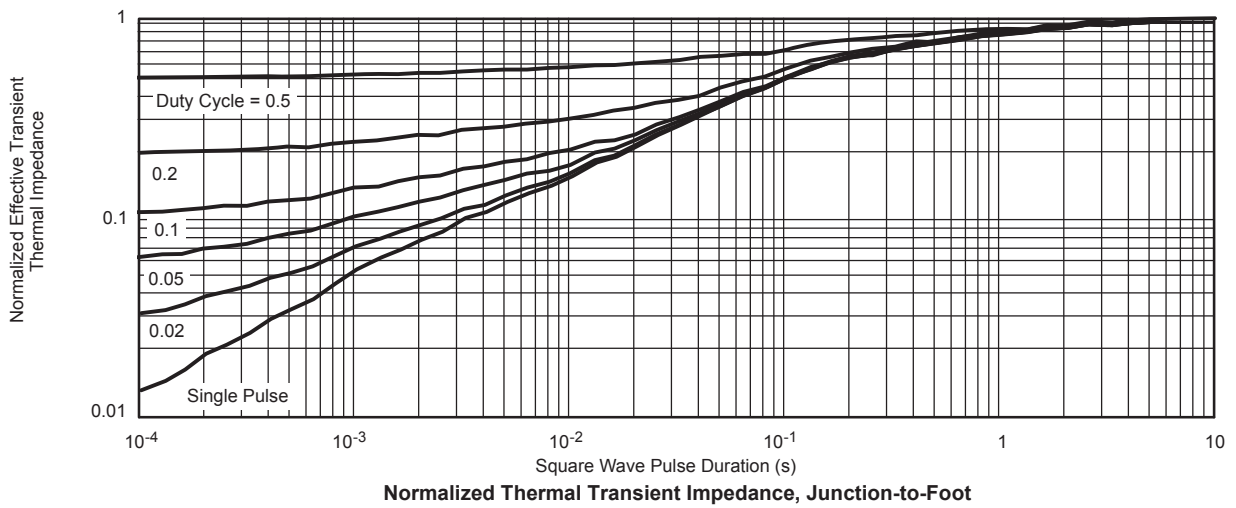
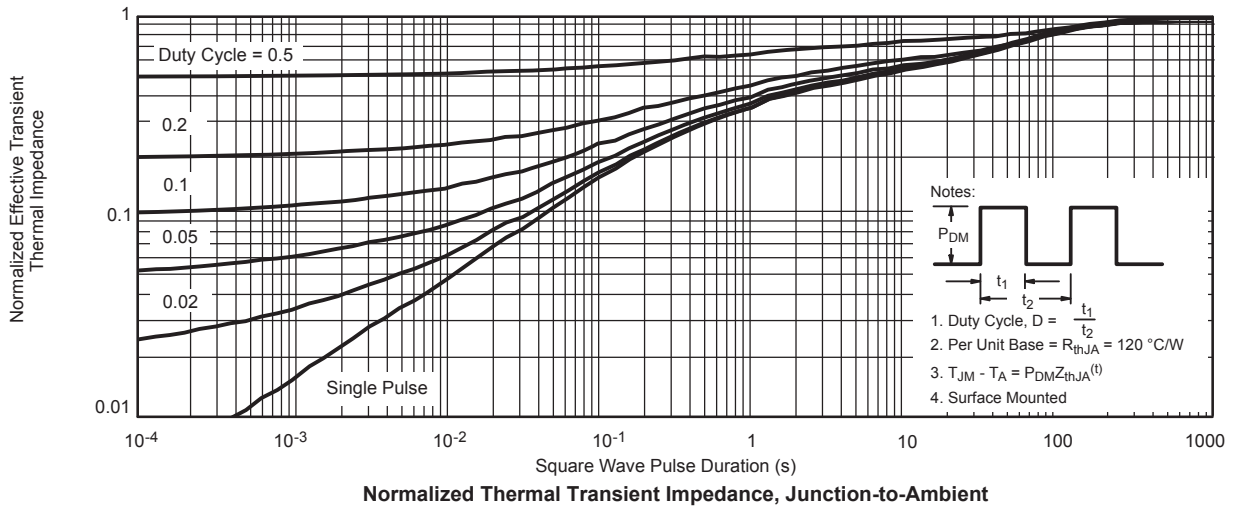
Safe Operating Area, Junction-to-Ambient

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

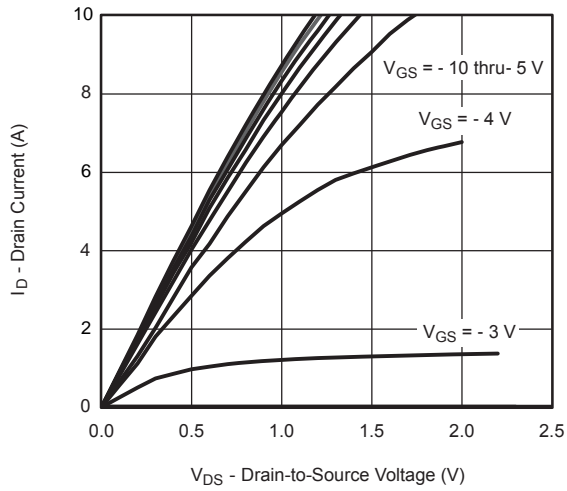


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

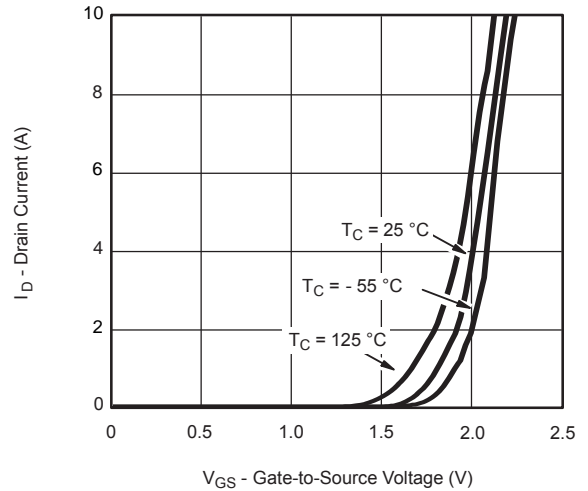
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



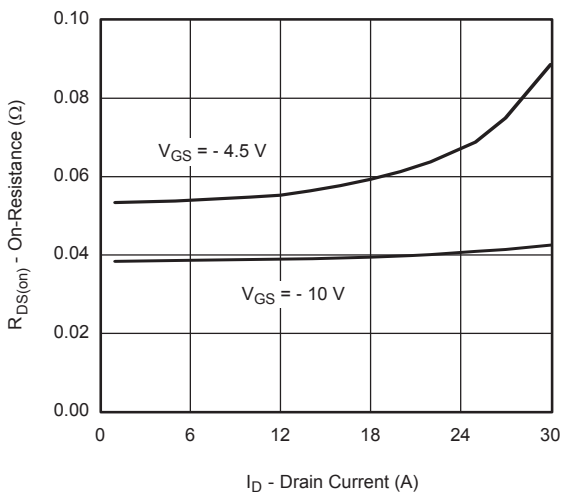
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



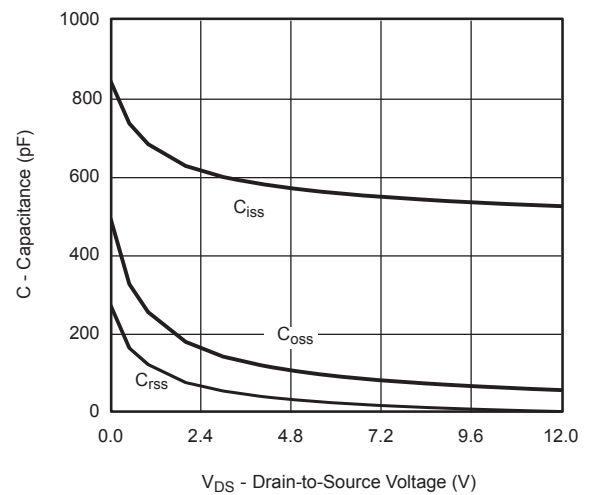
Output Characteristics



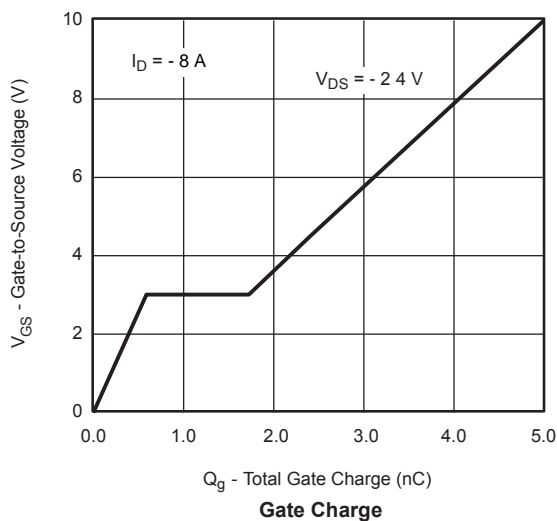
Transfer Characteristics



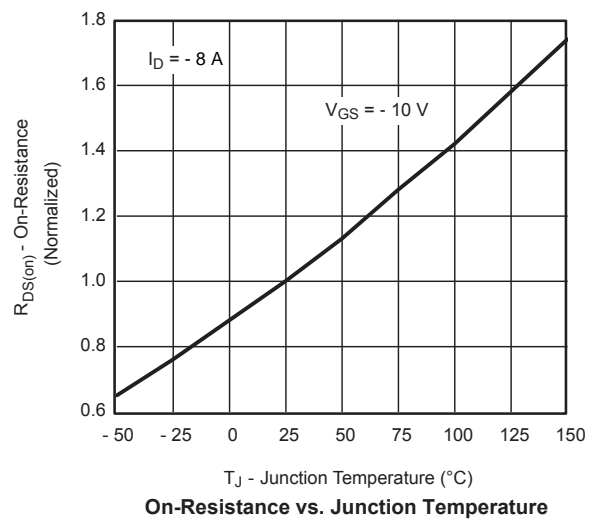
On-Resistance vs. Drain Current



Capacitance

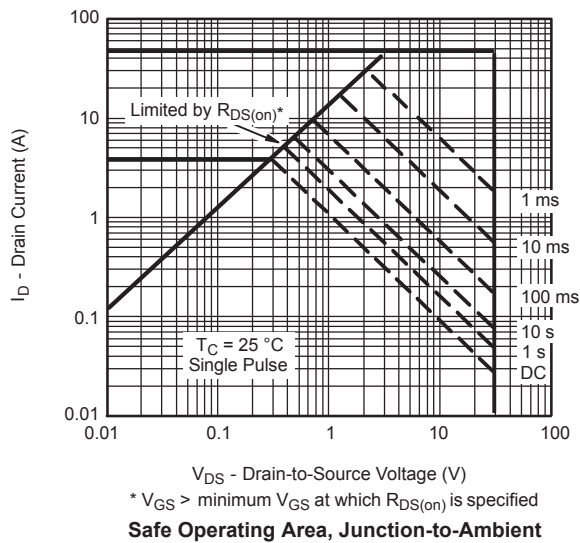
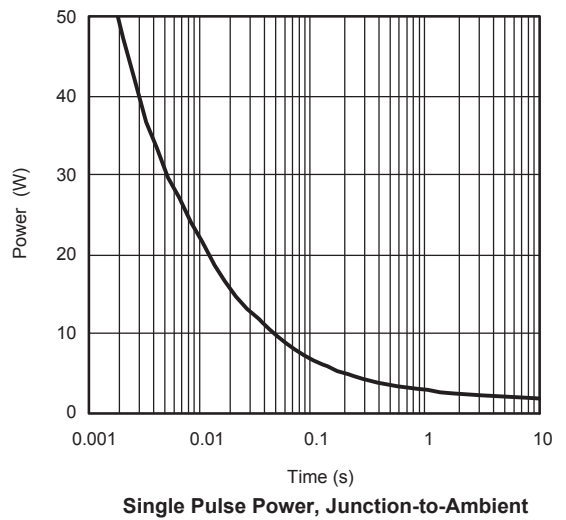
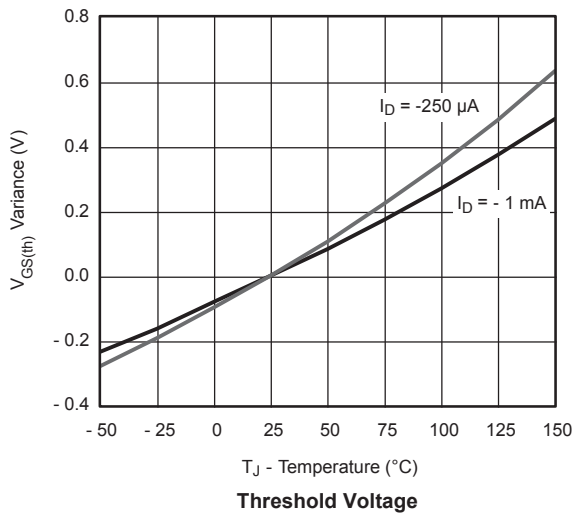
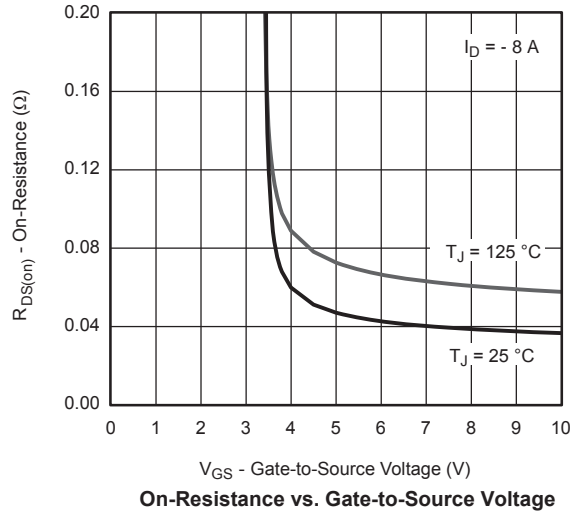
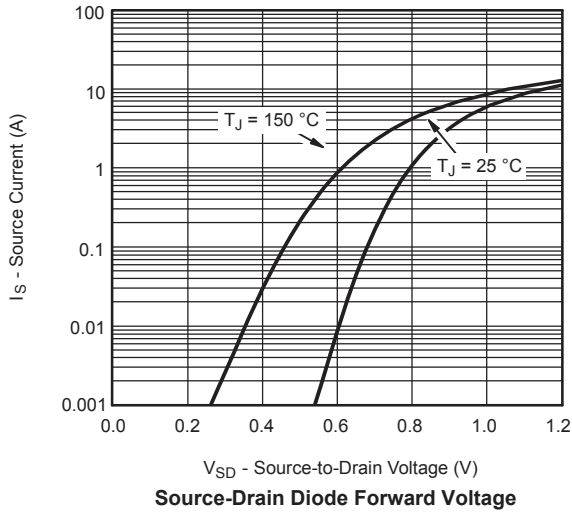


Gate Charge

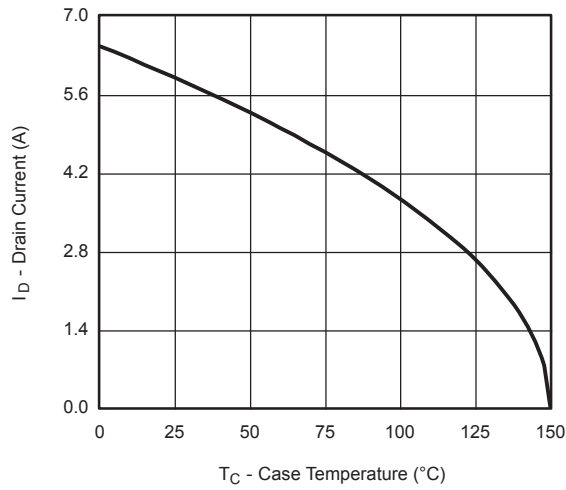


On-Resistance vs. Junction Temperature

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

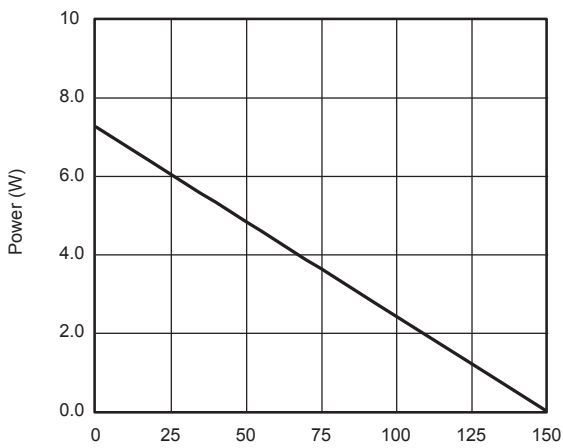


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



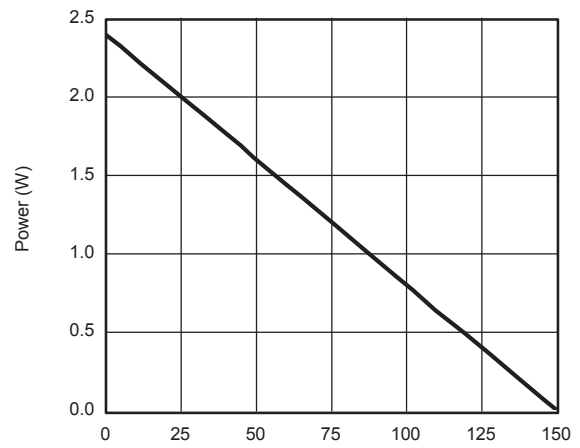
T_C - Case Temperature (°C)

Current Derating*



T_C - Case Temperature (°C)

Power Derating, Junction-to-Foot

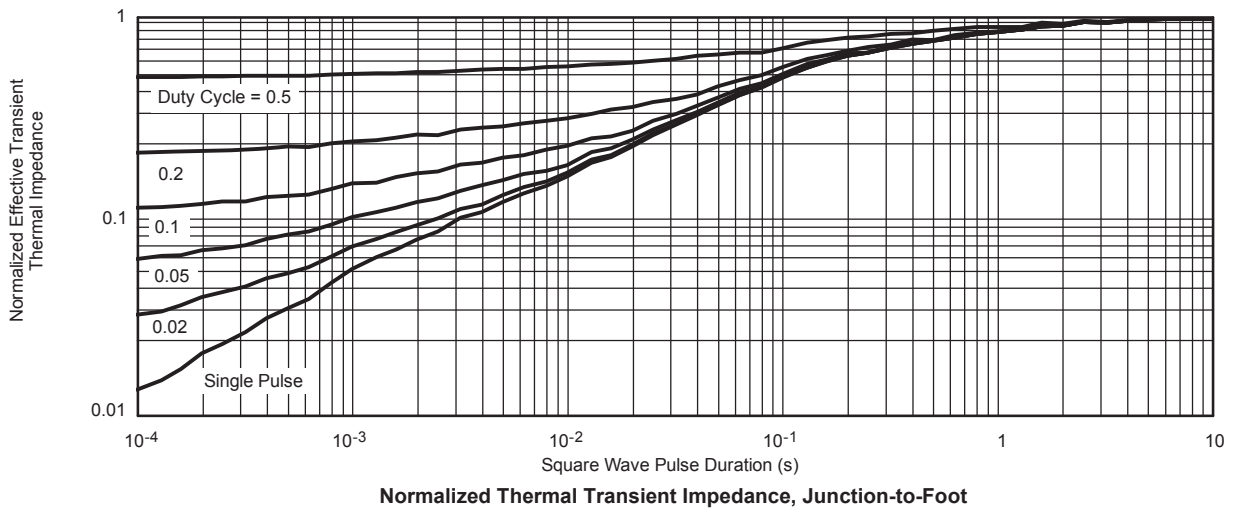
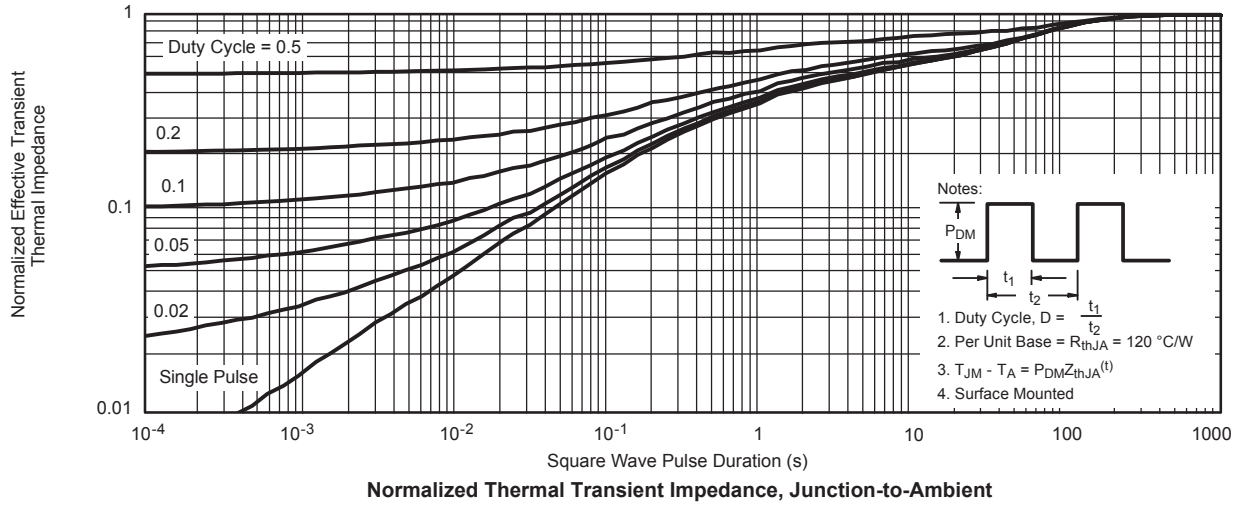


T_A - Ambient Temperature (°C)

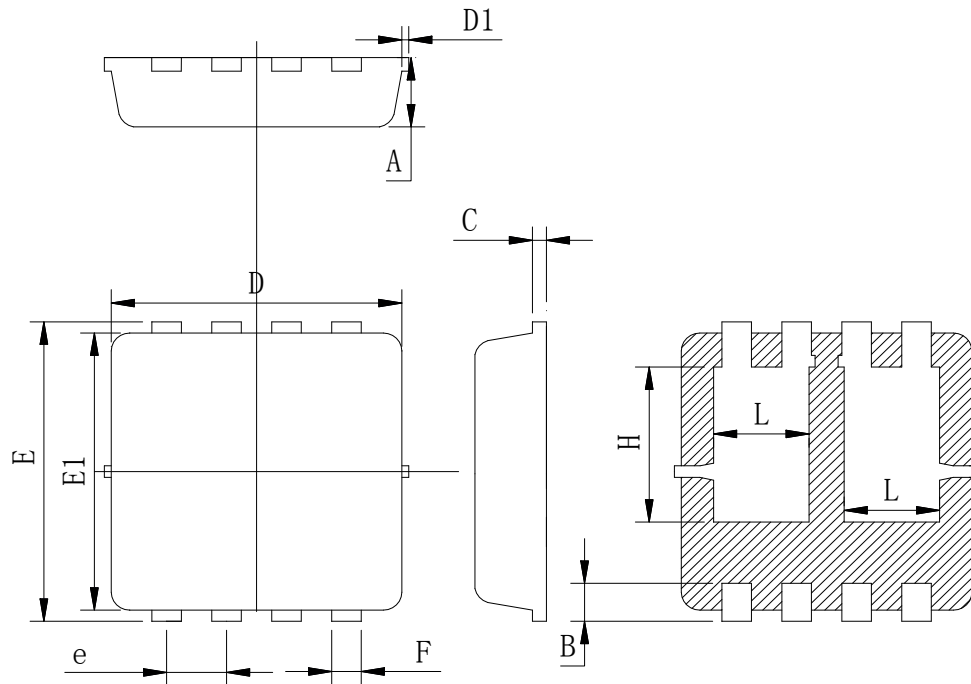
Power Derating, Junction-to-Ambient

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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



PDFN 3.3X3.3-D PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Typ	Max
A	0.680	0.775	0.920
B	0.25	0.38	0.55
C	0.08	0.15	0.25
D	2.95	3.10	3.25
D1			0.12
E	3.20	3.30	3.40
E1	2.85	3.00	3.15
e	0.50	0.65	0.80
F	0.23	0.32	0.41
H	1.53	1.73	1.93
L	0.83	1.03	1.23

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